



## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Ι <sub>D</sub> T <sub>C</sub> = +25°C
700V	$1.3\Omega @ V_{GS} = 10V$	4.6A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

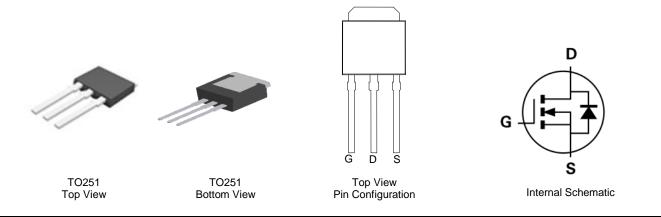
# N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features and Benefits**

- Low On-Resistance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(2)</sup>
- Weight: 0.33 grams (Approximate)



### Ordering Information (Note 4)

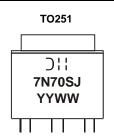
	Part Number	Case	Packaging		
DMJ70H1D3SJ3		TO251	75 Pieces/Tube		
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.					

EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Halogen - and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>
<1000ppm antimony compounds.</li>

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

## **Marking Information**



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# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	700	V	
Gate-Source Voltage	V <sub>GSS</sub>	±30	V	
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		ID	4.6 2.9	A
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	3.0	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	5.4	А	
Avalanche Current (Note 7)	L = 60mH	I <sub>AS</sub>	1.1	А
Avalanche Energy (Note 7) L = 60mH		E <sub>AS</sub>	40	mJ
Peak Diode Recovery dv/dt (Note 7)		dv/dt	5	V/ns

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>C</sub> = +25°C	Р	41	W
	T <sub>C</sub> = +100°C	PD	16	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>OJA</sub>	79	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R <sub>OJC</sub>	3.0	C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

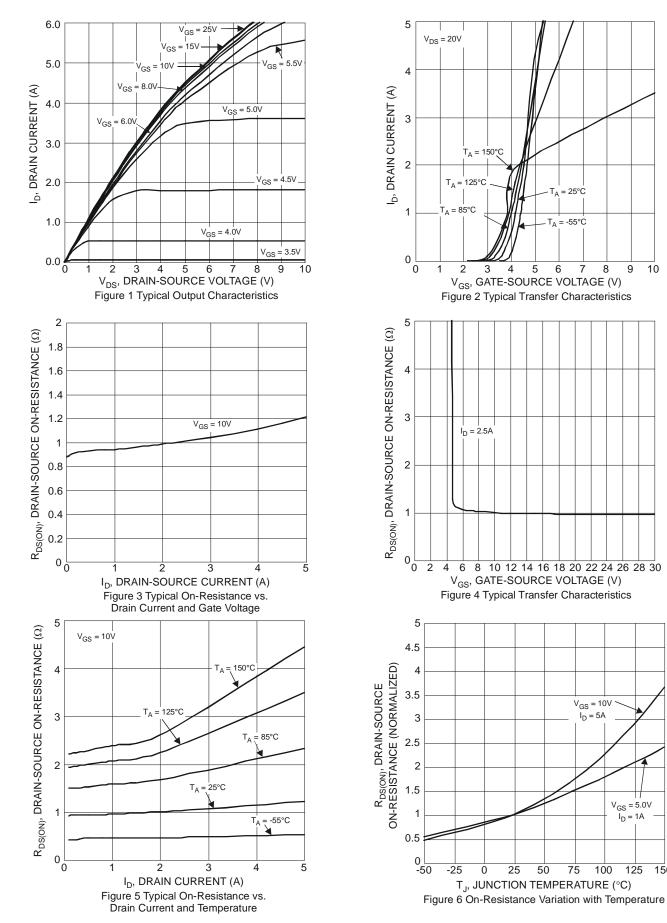
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	•,		. 76		•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	700			V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> = 700V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>		_	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•		•	•	•	·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	2.9	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.0	1.3	Ω	$V_{GS} = 10V, I_D = 2.5A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.9	1.3	V	$V_{GS} = 0V, I_S = 5A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	CISS	_	351	_			
Output Capacitance	Coss	_	66	_	pF	$V_{DS} = 50V$ , f = 1MHz, $V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	1.1	_		VGS = 0V	
Gate Resistance	R <sub>G</sub>	_	3.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Q <sub>G</sub>	_	13.9	_			
Gate-Source Charge	Q <sub>GS</sub>	_	1.9	_	nC	$V_{DD} = 560V, I_D = 5A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q <sub>GD</sub>	_	8.5	_		$v_{GS} = 10v$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.5	_			
Turn-On Rise Time	t <sub>R</sub>	_	11.6	_		$V_{DD}$ = 350V, $V_{GS}$ = 10V, R <sub>G</sub> = 4.7 $\Omega$ , I <sub>D</sub> = 2.5A	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	24.5	_	ns		
Turn-Off Fall Time	tF	_	10	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>		212		ns		
Body Diode Reverse Recovery Time $(T_J = +150^{\circ}C)$	t <sub>RR</sub>		251		ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		1.8		μC	$I_{\rm S} = 5$ A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge $(T_J = +150^{\circ}C)$	Q <sub>RR</sub>		2.3		μC	1	

Notes: 5. Device mounted on infinite heatsink.

Bovice mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
Guaranteed by design. Not subject to production testing.
Short duration pulse test used to minimize self-heating effect.



10

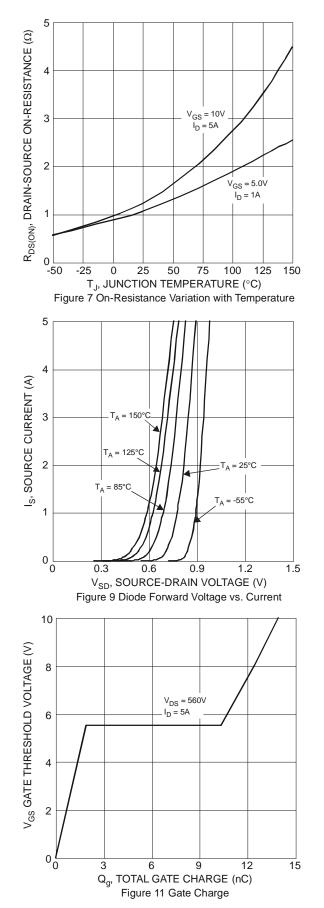


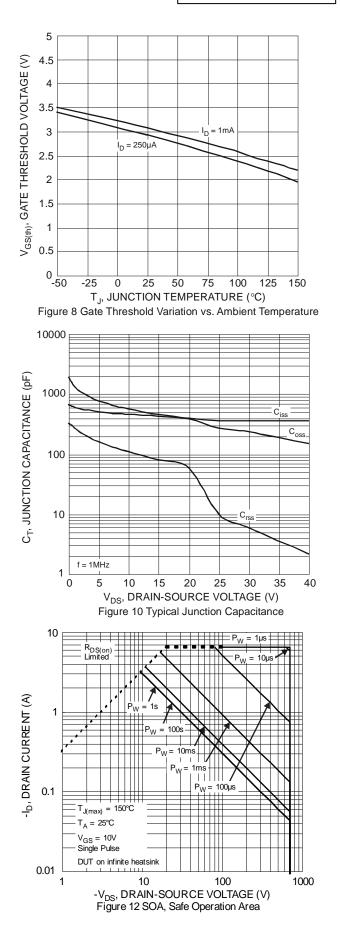
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150

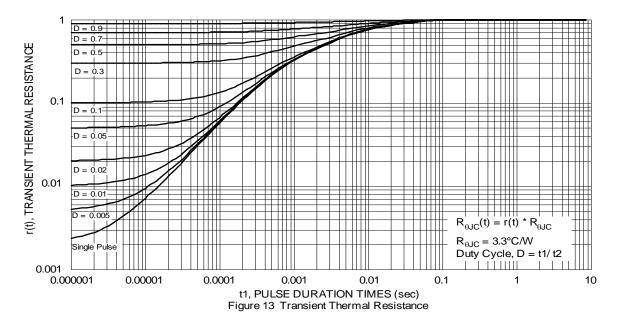






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# **Package Outline Dimensions**

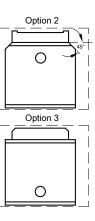
Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.

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A2

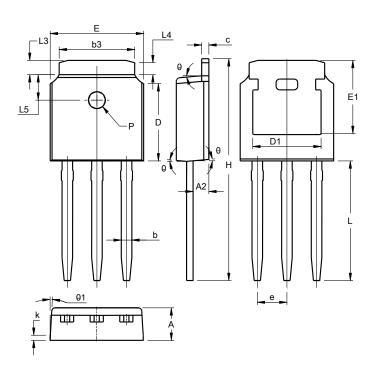
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Π



TO251							
Dim	Min	Max					
Α	2.200	2.400					
A2	0.890	1.150					
A3	0.450	0.550					
В	0.550 0.740						
С	0.450	0.570					
D	6.400	6.750					
D2	5.200	5.400					
ш	5.950	6.250					
E2	0.900	1.250					
E	2.240	2.340					
e1	4.430	4.730					
L	8.900	9.500					
All Dimensions in mm							

TO251 (Type TH)



TO251 (Type TH)						
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b3	5.20	5.50	5.33			
с	0.43	0.63	0.53			
D	5.98	6.22	6.10			
D1	5	5.30 REF	=			
е	2	.286 BS	С			
E	6.40	6.80	6.60			
E1	4.63	5.03	4.83			
н	16.22	16.82	16.52			
k	Ū	0.40REF	-			
L	9.15	9.65	9.40			
L3	0.88	1.28	1.02			
L4	0.75 REF					
L5	1.65	1.95	1.80			
PØ	1.20					
θ	5°	9°	7°			
θ1	5°	9°	7°			
All Dimensions in mm						



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